● General Description

The CH50N06D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

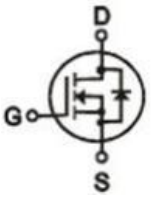
● Features

- ■ Advance high cell density Trench technology
- ■Low $R_{DS(ON)}$ to minimize conductive loss
- ■Low Gate Charge for fast switching
- ■Low Thermal resistance

●Application

- ■MB/VGA Vcore
- ■SMPS 2nd Synchronous Rectifier
- ■POL application
- ■BLDC Motor driver

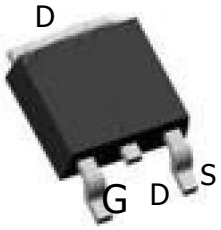
● Product Summary



V_{DS} =60V

$R_{DS(ON)}$ =9.5mΩ

I_D =50A



RoHS

TO-252

●Ordering Information:

Part NO.	CH50N06
Marking	CH50N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

●Absolute Maximum Ratings (T_C =25℃)

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	25	V
Continuous Drain Current	I_D@TC=25℃	50	A
	I_D@TC=75℃	38	A
	I_D@TC=100℃	32	A
Pulsed Drain Current ①	I_{DM}	150	A
Total Power Dissipation(TC=25℃)	P_D@TC=25℃	70	W
Total Power Dissipation(TA=25℃)	P_D@TA=25℃	2.8	W
Operating Junction Temperature	T_J	-55 to 175	℃
Storage Temperature	T_{STG}	-55 to 1755	℃
Avalanche Current	I_{AS} I_{AR}	40	A

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.83	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	45	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V,I_D =250uA	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	2.0		4.0	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=60V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V ,V_{DS} =0V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=40A		9.5	11.5	mΩ
Forward Transconductance	g_{FS}	V_{DS} =25V, I_D=10A		18		s
Source-drain voltage	V_{SD}	Is=24A		0.85	0.99	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	2170	-	pF
Output capacitance	C_{oss}		-	180	-	
Reverse transfer capacitance	C_{rss}		-	140	-	

●Gate Charge characteristics(Ta= 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	V_{DD} =30V	-	40	-	nC
Gate - Source charge	Q_{gs}	I_D = 15A	-	10	-	
Gate - Drain charge	Q_{gd}	V_{GS} = 10V	-	13	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Output Characteristics

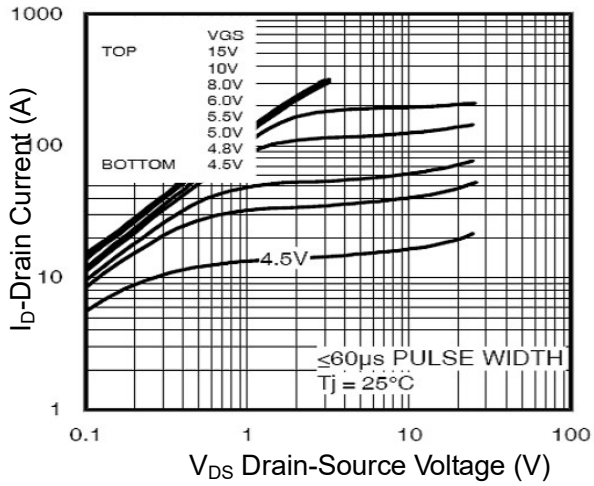


Figure2. Transfer Characteristics

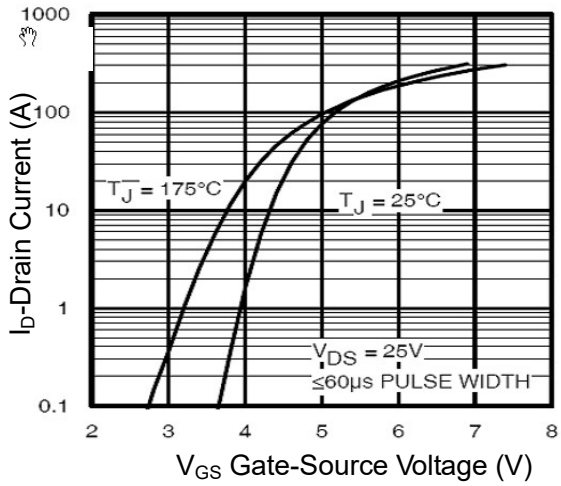
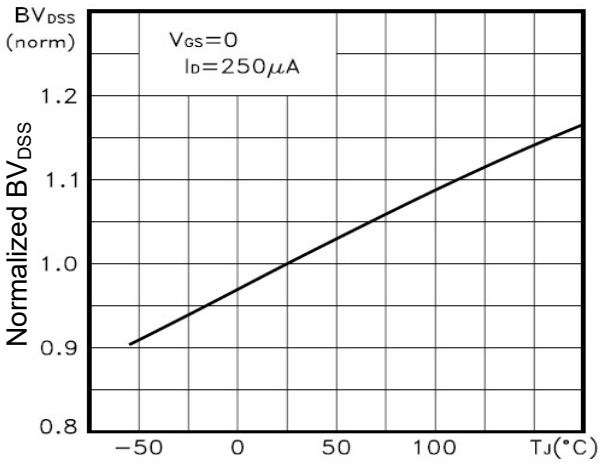
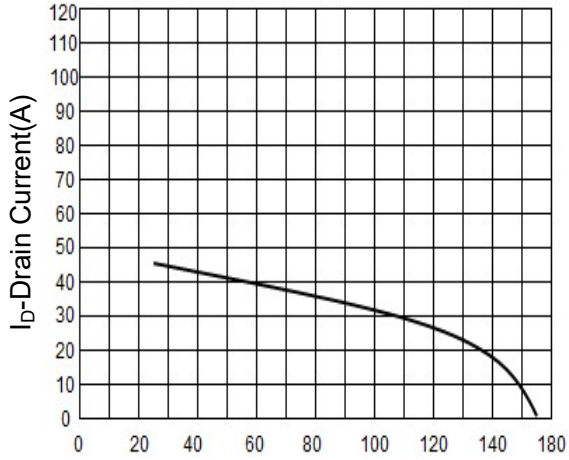


Figure3. BVDSS vs Junction Temperature



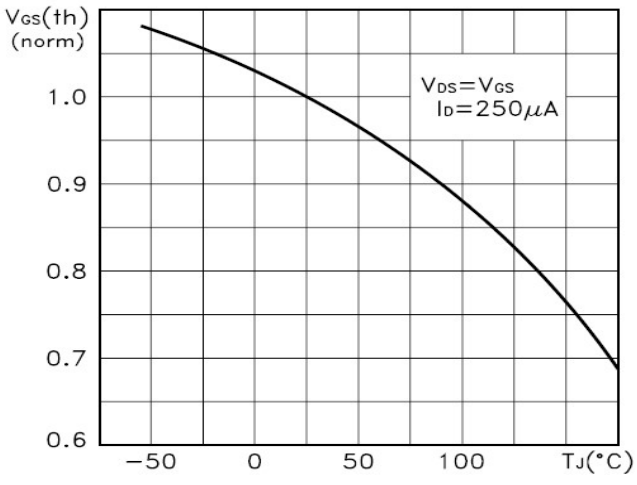
TJ-Junction Temperature(℃)

Figure4. ID vs Junction Temperature



TJ-Junction Temperature(℃)

Figure5. VGS(th) vs Junction Temperature



TJ-Junction Temperature(℃)

Figure6. Rdson Vs Junction Temperature

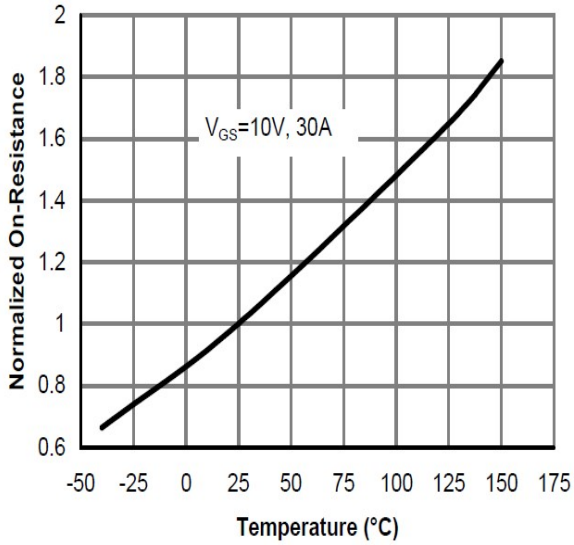
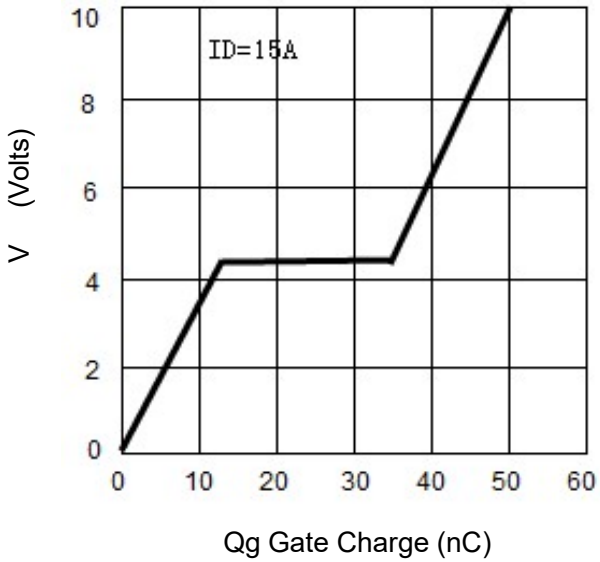


Figure7. Gate Charge



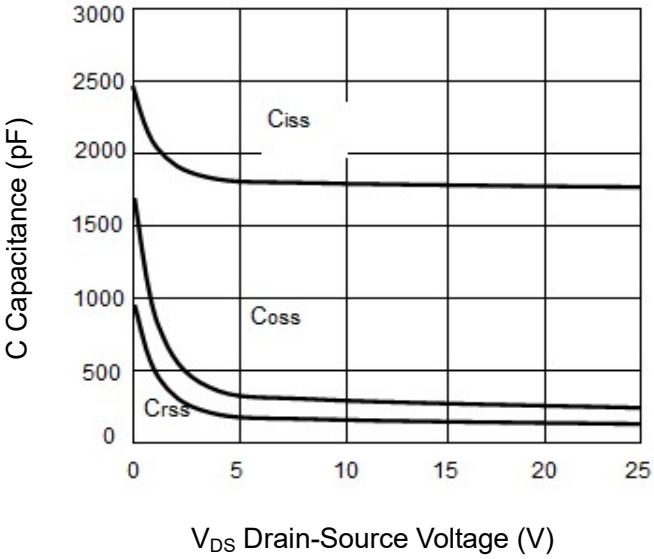


Figure9. Source- Drain Diode Forward

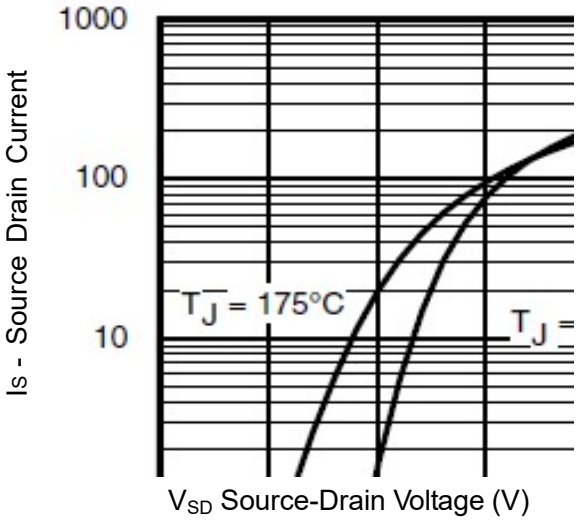


Figure10. Safe Operation Area

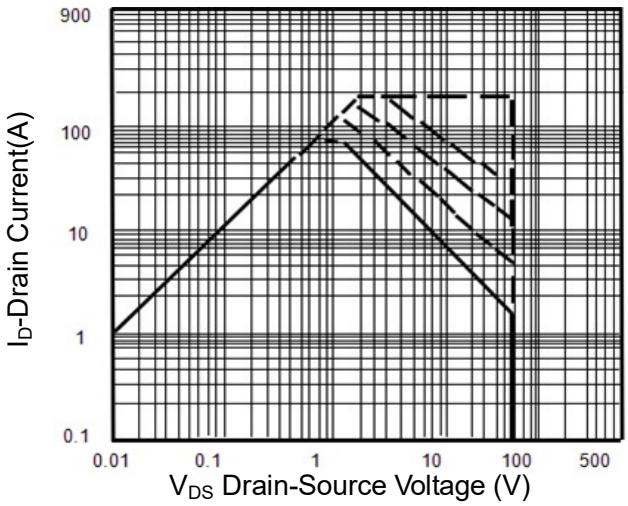
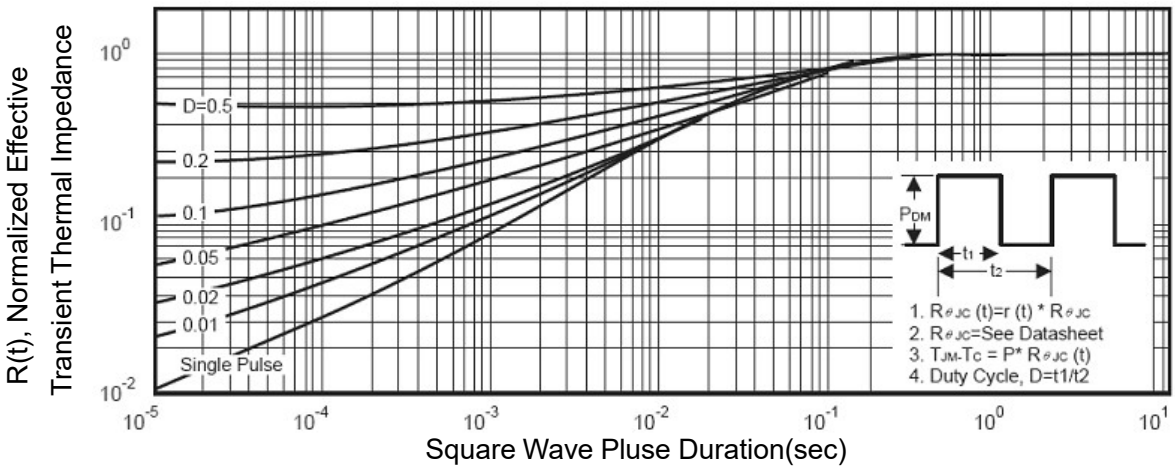
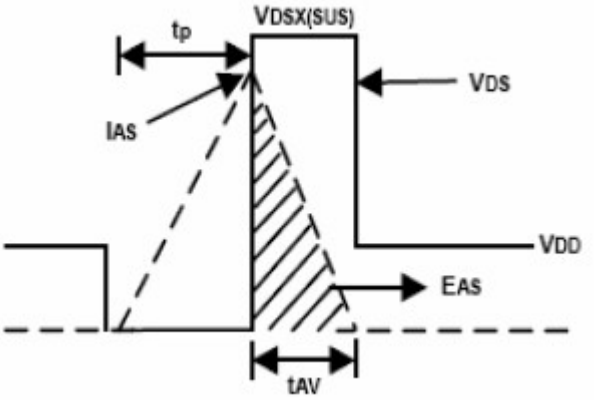


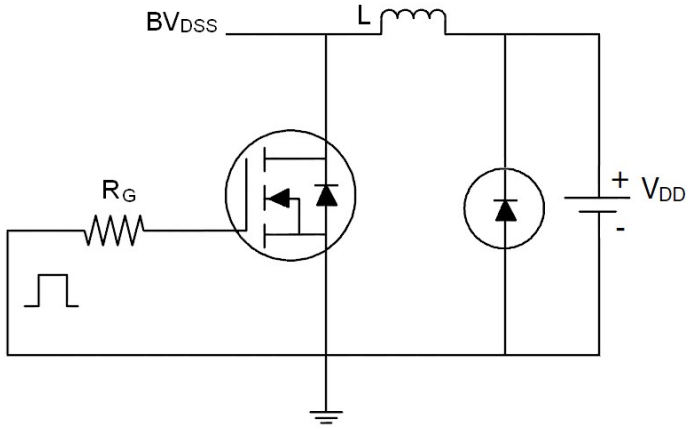
Figure11. Normalized Maximum Transient Thermal Impedance



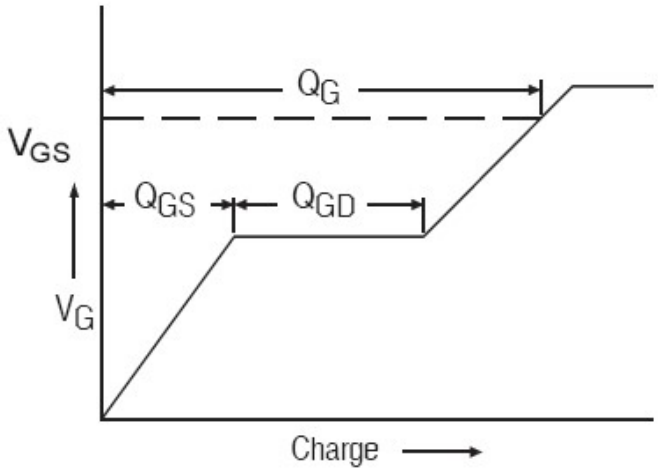
Test Circuit

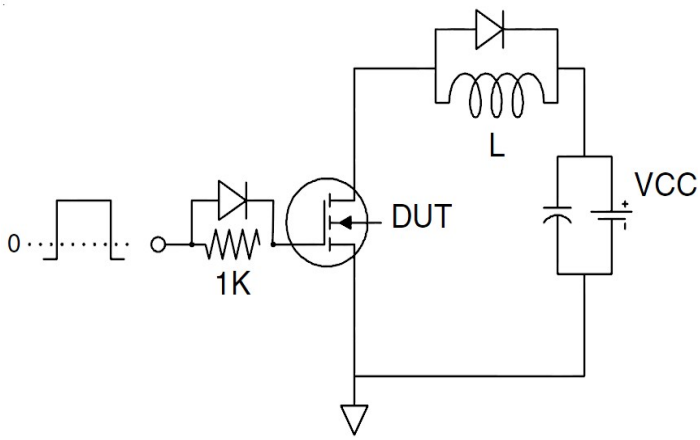
1） E_{AS} Test Circuits



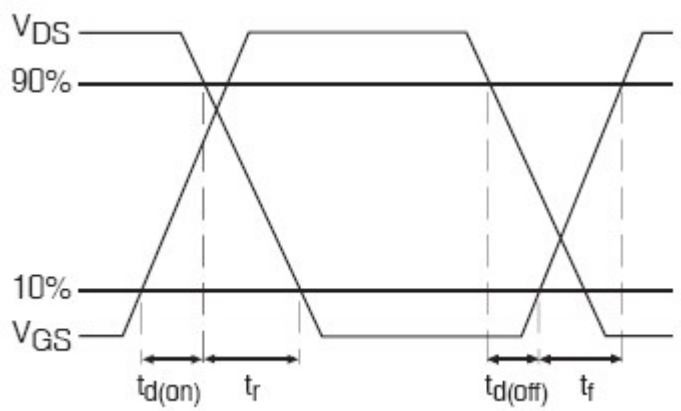


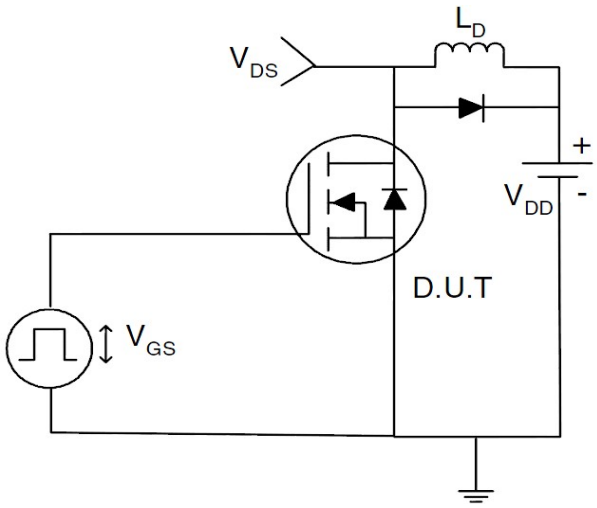
2）Gate Charge Test Circuit:





3）Switch Time Test Circuit:





●Dimensions(TO-252)

Unit：mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23